

**AUI]a i a 'FUh]b[g** ( $T_a=25$  Unless otherwise specified)

D5F5A9H9F'	GMA6C@	IB-H	M6G@'\$\$, 5
Device marking code			YBSL3008A
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	V	800
Maximum RMS Voltage	$V_{RMS}$	V	560
Maximum DC blocking Voltage	$V_{DC}$	V	800
Average rectified output current @60Hz sine wave, R-load, $T_c=125$	$I_o$	A	3.0
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave, 1 cycle, $T_j=25$	$I_{FSM}$	A	120
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, $T_j=25$			240
Current squared time @1ms $t < 8.3ms$ $T_j=25$ Rating of per diode	$I^2t$	$A^2s$	59.8
Storage temperature	$T_{stg}$		-55 ~ +150
Junction temperature	$T_j$		-55 ~ +150

**9'YWhf]WU' 7 \UfUWhYf]gh]Wg**  $T_a=25$  Unless otherwise specified

D5F5A9H9F'	GMA6C@	IB-H	H9GH'7CB8-H-CBG	Ajb'	Hmd'	AUI'
Instantaneous forward voltage drop per diode	$V_F$	V	$I_{FM}=1.5A$	0.7	0.87	0.92
DC reverse current at rated DC blocking voltage per diode	$I_R$	$\mu A$	$T_j=25$	-	0.1	5
			$T_j=125$	-	35	100
Junction capacitance	$C_j$	$\mu F$	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	20	38	60



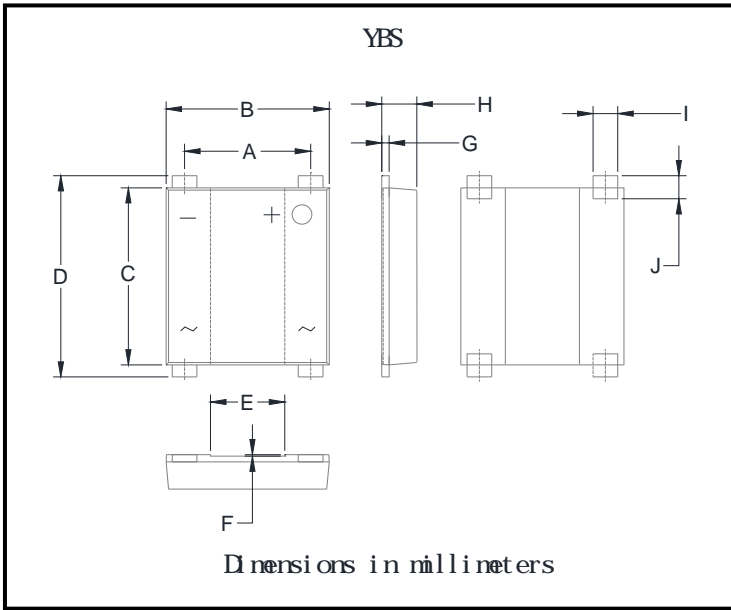
H\YfaU`7\UfUWhYf]gh]Wg` Ta=25 Unless otherwise specified

D5F5A9H9F`

GMA6C@`



C i h`]bY`8]a Ybg]cbg`



M6G`		
Dim	Min	Max
A	5.00	5.20
B	6.50	6.70
C	7.20	7.40
D	7.90	8.60
E	2.90	3.10
F	0.04	0.08
G	0.27	0.40
H	1.30	1.50
I	0.95	1.15
J	0.70	1.05

'Gi [ [YghYX`dUX`Umc i h`



8]a`	A]b`
P1	9.15
P2	7.10
Q1`	1.80
Q2`	2.00

